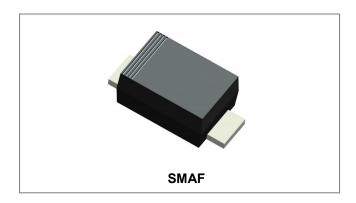






RS3AAF THRU RS3MAF FAST RECOVERY RECTIFIERS



Features

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- · Easy to pick and place
- Fast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/ EU directives
- This is a Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: JEDEC SMAF molded plastic body
- Terminals: leads solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Weight: 0.038 gramsMounting Position: Any

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Type Number	Symbol	RS3A AF	RS3B AF	RS3D AF	RS3G AF	RS3J AF	RS3K AF	RS3M AF	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _{DC}	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{RMS}	35	70	140	280	420	560	700	\ \
verage forward rectified output current @T _L = 100°C I _O 3.0			Α						
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	_{FSM} 90			А				
Forward Voltage @I _F =3.0A	V _F				1.3				V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 125°C	I _{RM}				5.0 150				μA
Maximum Reverse Recovery Time (Note 1)	Trr				160				ns
Typical Junction Capacitance (Note 2)	CJ				60				pF
Typical Thermal Resistance (Note 3)	R _{0JA}				60				°C/W
Operating and Storage Temperature Range	T _J , T _{STG}			-	65 to +1	50			°C

Note: 1. Measured with IF = 0.5 A, IR = 1 A, Irr = 0.25 A

- 2. Measured at 1MHz and applied reverse voltage of 4V D.C
- 3. P.C.B. mounted with 0.5 X 0.5" (12.7 X 12.7 mm) copper pad areas.
 - China Germany Korea Singapore United States
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Ratings and Characteristics Curves

Fig.1 Forward Current Derating Curve

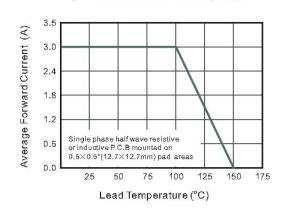


Fig.2 Typical Reverse Characteristics

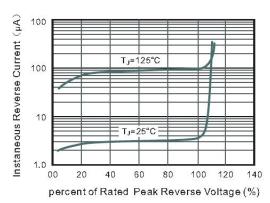


Fig.3 Typical Instaneous Forward Characteristics

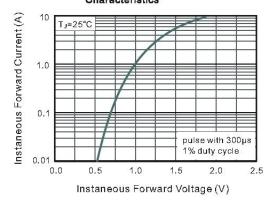


Fig.4 Typical Junction Capacitance

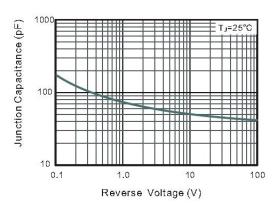
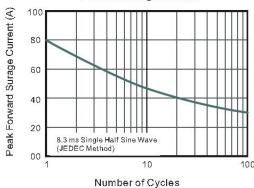


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current



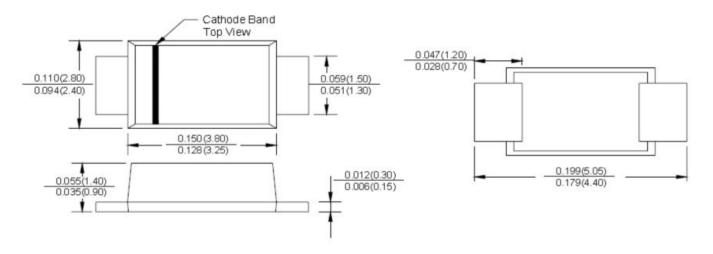
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Mechanical Dimensions SMAF(Millimeters/Inches)

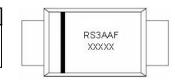


Ordering Information

Device Package		Shipping			
RS3AAF					
THRU	SMAF (Pb-Free)	3000pcs / reel			
RS3MAF	, , ,				

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

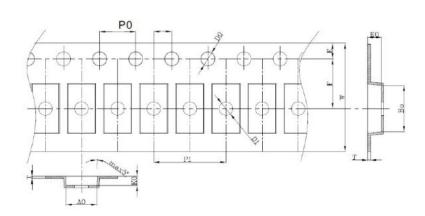
Marking Diagram



Where XXXXX is YYWWL

RS3AAF = Part Name = Year WW = Week = Lot Number

Carrier Tape Specification SMAF



SYMBOL	Millimeters				
STWIDUL	Min.	Max.			
A0	2.83	3.03			
B0	2.23	5.43			
K0	1.23	1.43			
P0	3.90	4.10			
P1	3.90	4.10			
P2	1.90	2.10			
T	0.17	0.23			
Е	1.63	1.83			
F	5.45	5.65			
D0	1.50	1.60			
D1	1.45	1.55			
W	11.70	12.30			

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